WHAT IS CLAIMED IS:

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- 1. A semiconductor device, comprising:
- a thin film transistor formed on an insulating surface of a substrate; and
- a diamond-like carbon film formed on a back surface of the substrate.
- 2. A semiconductor device according to claim 1, wherein the substrate is a quartz substrate.

3. A device according to claim 1, wherein the diamond-like

carbon film has a specific resistance of 10^7 to $10^{14}~\Omega cm$.

- 4. A device according to claim 1, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.
- 5. A device according to claim 1, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type projector, and a rear type projector.
 - 6. A semiconductor device, comprising:

a diamond-like carbon film formed on an insulating surface of a substrate;

an underlayer film formed on the diamond-like carbon film;

a thin film transistor formed on the underlayer film.

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- 7. A device according to claim 6, wherein the substrate is a quartz substrate.
- 8. A device according to claim 6, wherein the diamond-like carbon film has a specific resistance of 10^7 to 10^{14} Ω cm.
 - 9. A device according to claim 6, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.
 - 10. A device according to claim 6, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type projector, and a rear type projector.
 - 11. A semiconductor device, comprising:

a thin film transistor formed over an substrate having an

insulating surface;

an interlayer insulating film formed over the thin film transistor; and

- a diamond-like carbon film formed on the interlayer insulating film.
 - 12. A device according to claim 11, further comprising a transparent conductive film formed over the diamond-like carbon film.

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- 13. A device according to claim 11, wherein the diamond-like carbon film has a thickness of 5 to 100 nm.
- 14. A device according to claim 11, wherein the diamond-like carbon film has a specific resistance of 10^7 to $10^{14}~\Omega$ cm.
 - 15. A device according to claim 11, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.

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16. A device according to claim 11, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type

projector, and a rear type projector.

17. A method of manufacturing a semiconductor device, comprising the steps of:

forming a thin film transistor on an insulating surface of a substrate; and

forming a diamond-like carbon film on a back surface of the insulating substrate.

- 18. A method according to claim 17, wherein the substrate is a quartz substrate.
 - 19. A method according to claim 17, wherein the diamond-like carbon film has a specific resistance of 10^7 to 10^{14} Ω cm.

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20. A method according to claim 17, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.

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21. A method according to claim 17, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type projector, and a rear type projector.

22. A method of manufacturing a semiconductor device, comprising the steps of:

forming a diamond-like carbon film on an insulating surface

of a substrate;

forming an underlayer film on the diamond-like carbon film;

forming a thin film transistor on the underlayer film.

- 23. A method according to claim 22, wherein the substrate is a quartz substrate.
 - 24. A method according to claim 22, wherein the diamond-like carbon film has a specific resistance of 10^7 to 10^{14} Ω cm.

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- 25. A method according to claim 22, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.
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- 26. A method according to claim 22, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type projector, and a rear type projector.

27. A method of manufacturing a semiconductor device, comprising the steps of:

forming a thin film transistor over a substrate having an insulating surface;

forming an interlayer insulating film covering the thin film transistor; and

forming a diamond-like carbon film over the interlayer insulating film.

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- 28. A method according to claim 27, further comprising a step of forming a transparent conductive film on the diamond-like carbon film.
- 15 29. A method according to claim 27, the diamond-like carbon film has a thickness of 10 to 100 nm.
 - 30. A method according to claim 27, wherein the diamond-like carbon film has a specific resistance of 10^7 to $10^{14}~\Omega cm$.

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31. A method according to claim 27, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.

32. A method according to claim 27, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type projector, and a rear type projector.